
Table of Contents

1. Introduction
2. MOS I-V Model
 - 2.1. *Floating Body Operation and Effective Body Potential*
 - 2.2. *Threshold Voltage in the High V_{bs} Regime*
 - 2.2.1. Linear Extrapolation for the Square-Root Expression
 - 2.2.2. Width Dependence of the Body Effect
 - 2.3. *Bulk Charge Effect in the High V_{bs} Regime*
 - 2.4. *Asymmetric and Bias-Dependent Source/Drain Resistance Model*
 - 2.5. *Single Drain Current Equation*
3. Body Currents Model
 - 3.1. *Diode and Parasitic BJT Currents*
 - 3.2. *New Impact Ionization Current Equation*
 - 3.3. *Gate Induced Drain Leakage Current*
 - 3.4. *Oxide Tunneling Current*
 - 3.5. *Body Contact Current*
 - 3.6. *Body Contact Parasitics*
4. MOS C-V Model
 - 4.1. *Charge Conservation*
 - 4.2. *Intrinsic Charges*
 - 4.3. *Source/Drain Junction Charges*
 - 4.4. *Extrinsic Capacitances*
 - 4.5. *Body Contact Parasitics*

- 5. Temperature Dependence and Self-Heating**
 - 5.1. *Temperature Dependence***
 - 5.2. *Self-Heating Implementation***
- 6. BSIMSOI - A Unified Model for PD and FD SOI MOSFETs**
 - 6.1. *BSIMSOI Framework and Built-In Potential Lowering Model***
 - 6.2. *Verification***
 - 6.3. *Model Selector SOIMOD***
- 7. BSIMSOI RF Model**
 - 7.1 *Gate Electrode and Intrinsic-Input Resistance (IIR) Model***
 - 7.2 *Body Resistance Network***
- 8. BSIMSOI Noise Model**
 - 8.1 *Flicker Noise models***
 - 8.2 *Thermal Noise models***
 - 8.3 *Other Improvement on Noise Model***
- 9. BSIMSOI Stress Model**
 - 9.1 *Mobility Related Equations***
 - 9.2 *Vth Related Equations***
 - 9.3 *Multiple Finger Device***
- 10. References**
- 11. Appendix A: Model Instance Syntax**
- 12. Appendix B: Model Parameter List**
- 13. Appendix C: Equation List**
- 14. Appendix D: Parameter Extraction**

15. Appendix E: Model Parameter Binning